

# $16K \times 1$ CMOS STATIC RAM

- 20, 25, AND 35 ns ADDRESS ACCESS TIME
- EQUAL ACCESS AND CYCLE TIMES
- 20-PIN, 300 MIL PLASTIC AND CERAMIC DIP
- ALL INPUT AND OUTPUT PINS TTL COMPATI-BLE, LOW CAPACITANCE, AND PROTECTED AGAINST STATIC DISCHARGE
- 50 µA CMOS STANDBY CURRENT (MK41H67)
- HIGH SPEED CHIP SELECT (MK41H66)
- JEDEC STANDARD PINOUT

# MK41H66 TRUTH TABLE

ĈE	WE	Mode	DQ	Power
н	X	Deselect	High Z	Active
L	L	Write	High Z	Active
L	Н	Read	Data Out	Active

X = Don't Care

# MK41H67 TRUTH TABLE

<u>CS</u>	WE	Mode	DQ	Power
н	X	Deselect	High Z	Standby
L	L	Write	High Z	Active
L	н	Read	Data Out	Active

#### DESCRIPTION

The MK41H66 and MK41H67 feature fully static operation requiring no external clocks or timing strobes, and equal address access and cycle times. Both require only a single  $+5V \pm 10$  percent power supply. Both devices are fully TTL compatible.

The MK41H67 has a Chip Enable power down feature which automatically reduces power dissipation when the CE pin is brought inactive (high). Standby power can be further reduced to microwatt levels by holding the Address and CE pins at full supply rail voltages.

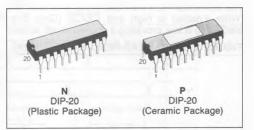


FIGURE	1. PIN	CONNECTIONS	
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			7	
A	1		20 V <sub>CC</sub>	
A,	2		19 A <sub>13</sub>	
A2	3 🗆		18 A <sub>12</sub>	
A3	4 🗆		17 A11	
A4	5 🗆	MK41H66	16 A <sub>10</sub>	
A <sub>5</sub>	6 🗆		🗆 15 A <sub>9</sub>	
A <sub>6</sub>	7 🗆		14 A <sub>8</sub>	
Q	8 🗆		13 A <sub>7</sub>	
WE	9 🗆		12 D	
GND	10 🗆		11 CS	
	1		1	
A <sub>0</sub>	1 [		20 V <sub>CC</sub>	
A,	2		19 A <sub>13</sub>	
A2	3 🗆		18 A <sub>12</sub>	
A3	4 🗆		17 A <sub>11</sub>	
A4	5	MK41H67	16 A <sub>10</sub>	
A <sub>5</sub>	6 🗆	meenior	🗆 15 A <sub>9</sub>	
A <sub>6</sub>	7 🗆		14 A <sub>8</sub>	
Q	8 🗆		13 A <sub>7</sub>	
WE	9 🗆		12 D	
GND	10 🗆		11 CE	
			1	

#### PIN NAMES

An - An - Address	WE - Write Enable
CE - Chip Enable	GND - Ground
(MK41H67)	V <sub>CC</sub> - + 5 volts
<u>CS</u> - Chip Select	D - Data In
(MK41H66)	Q - Data Out

The MK41H66 Chip Select pin provides a high speed chip select access, allowing fast read cycles despite decoder delays.

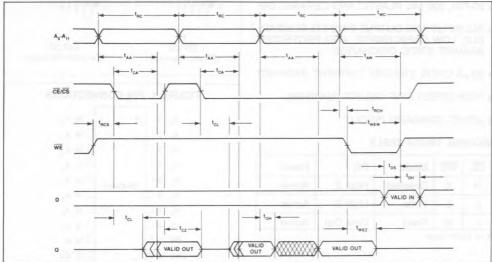
### **OPERATIONS**

#### **READ MODE**

The MK41H66/7 is in the Read Mode whenever WE (Write Enable) is high and CE/CS (Chip Enable/Select) is low, providing a ripple-through access

### FIGURE 2. READ-READ-READ-WRITE TIMING

to any one of 16,384 locations in the static storage array. Valid data will be available at the Data Output pin (Q) within  $t_{AA}$  after the last address input signal is stable, providing that the CE/CS access time is satisfied. If CE/CS access time is not met, data access will be measured from the limiting parameter ( $t_{CA}$ ) rather than the address. The state of the Data Output pin is controlled by the CE/CS, and WE control signals. The Q may be in an indeterminate state at  $t_{CL}$ , but the Q will always have valid data at  $t_{AA}$ .



## READ CYCLE TIMING AC ELECTRICAL CHARACTERISTICS

 $(0^{\circ}C \le T_A \le 70^{\circ}C) (V_{CC} = 5.0 \text{ V} \pm 10 \text{ percent})$ 

		MK41	16X-20	MK41H	16X-25	MK41	16X-35		
SYM	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
t <sub>RC</sub>	Read Cycle Time	20		25		35		ns	
t <sub>AA</sub>	Address Access Time		20		25		35	ns	1
t <sub>CL</sub>	Chip Enable to Low-Z (MK41H67)	5		5		5		ns	2
t <sub>CL</sub>	Chip Select to Low-Z (MK41H66)	5		5		5		ns	2
1 <sub>CA</sub>	Chip Enable Access Time (MK41H67)		20		25		35	ns	1
t <sub>CA</sub>	Chip Select Access Time (MK41H66)		10		12		15	ns	1
t <sub>RCS</sub>	Read Command Setup Time	0		0		0		ns	
t <sub>RCH</sub>	Read Command Hold Time	0		0		0		ns	
t <sub>он</sub>	Valid Data Out Hold Time	5		5		5		ns	1
t <sub>cz</sub>	Chip Enable to High-Z (MK41H67)	Ì	8		10		13	ns	2
t <sub>cz</sub>	Chip Select to High-Z (MK41H66)		7		8		10	ns	2
t <sub>WEZ</sub>	Write Enable to High-Z		8		10		13	ns	2

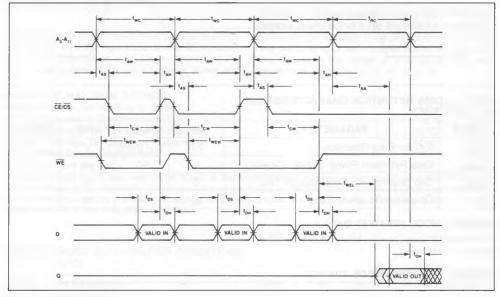


# WRITE MODE

The MK41H66/7 is in the Write Mode whenever the WE and CE/CS inputs are in the low state. CE/CS or WE must be high during address transitions. Addresses must be held valid throughout a write cycle. The Write begins with the concurrence of a low ON WE and CE/CS. Therefore,  $t_{AS}$  is referenced to

the latter occurring edge of CE/CS, or WE.

If the output is enabled (CE/CS is low), then WE will return the output to high impedance within  $t_{WEZ}$  of its falling edge. Data-In must remain valid  $t_{DH}$  after the rising edge of CE/CS or WE.



### FIGURE 3. WRITE-WRITE-WRITE-READ TIMING

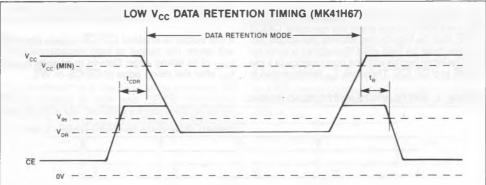
# WRITE CYCLE TIMING AC ELECTRICAL CHARACTERISTICS

 $(0^{\circ}C \le T_A \le 70^{\circ}C) (V_{CC} = 5.0 \text{ V} \pm 10 \text{ percent})$ 

		MK41I	16X-20	MK41	16X-25	MK41	16X-35		
SYM	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
twc	Write Cycle Time	20		25		35		ns	
t <sub>AS</sub>	Address Setup Time	0		0		0		ns	
t <sub>AW</sub>	Address Valid to End of Write	16		20		30		ns	
t <sub>AH</sub>	Address Hold after End of Write	0		0		0		ns	
t <sub>cw</sub>	Chip Enable/Select to End of Write	18		22		32		ns	
twew	Write Enable to End of Write	16		20		30		ns	
t <sub>DS</sub>	Data Setup Time	12		14		15		ns	
t <sub>DH</sub>	Data Hold Time	0		0		0		ns	
tWEL	Write Enable to Low-Z	5		5		5		ns	2



## FIGURE 4. DATA RETENTION TIMING



# LOW V<sub>CC</sub> DATA RETENTION CHARACTERISTICS

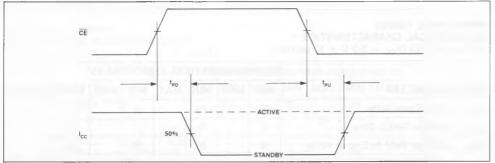
 $(0^{\circ}C \le T_A \le 70^{\circ}C)$ 

SYM	PARAMETERS	MIN	MAX	UNIT	NOTES
VDR	V <sub>CC</sub> for Data Retention	2.0	V <sub>CC</sub> (min)	V	7
ICCDR	Data Retention Power Supply Current	-	50	μΑ	7
t <sub>CDR</sub>	Chip Deselection to Data Retention Time	0	_	ns	
tR	Operation Recovery Time	t <sub>RC</sub>	-	ns	

# STANDBY MODE (MK41H67 Only)

The MK41H67 is in Standby Mode whenever  $\overline{CE}$  is held at or above  $V_{IH}.$ 

## FIGURE 5. STANDBY MODE TIMING



# STANDBY MODE AC ELECTRICAL CHARACTERISTICS

 $(0^{\circ}C \leq T_A \leq 70^{\circ}C) (V_{CC} = 5.0 \text{ V} \pm 10 \text{ percent})$ 

		MK41H67-20 MK41H67-25 MK41H67-35							
SYM	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
t <sub>PD</sub>	Chip Enable High to Power Down		20		25		35	ns	
t <sub>PU</sub>	Chip Enable Low to Power Up	0		0		0		ns	



## APPLICATION

The MK41H66/7 operates from a 5.0 volt supply. It is compatible with all standard TTL families on all inputs and outputs. The device should share a solid ground plane with any other devices interfaced with it, particularly TTL devices. Additionally, because the outputs can drive rail-to-rail into high impedance loads, the 41H66/7 can also interface to 5 volt CMOS on all inputs and outputs. Refer to the normalized performance curves that follow.

Since very high frequency current transients will be associated with the operation of the MK41H66/7, power line inductance must be minimized on the circuit board power distribution network. Power and ground trace gridding or separate power planes can be employed to reduce line inductance. Additionally, a high frequency decoupling capacitor should be placed next to each RAM. The capacitor should be 0.1  $\mu$ F or larger.

Though often times not thought of as such, the traces on a memory board are basically unterminated, low impedance transmission lines. As such they are subject to signal reflections manifested as noise, undershoots and excessive ringing. Series termination in close proximity to the TTL drivers can improve driver/signal path impedance matching. While experimentation most often proves to be the only practical approach to selection of series resistors, values in the range of 10 to 33 ohms often prove most suitable.

### ABSOLUTE MAXIMUM RATINGS\*

tended periods of time may affect reliability.

 Voltage on any pin relative to GND
  $-1.0 \ V \ to +7.0 \ V$  

 Ambient Operating Temperature ( $T_A$ )
  $0^{\circ}C \ to +70^{\circ}C$  

 Ambient Storage Temperature (Plastic)
  $-55^{\circ}C \ to +125^{\circ}C$  

 Ambient Storage Temperature (Ceramic)
  $-65^{\circ}C \ to +150^{\circ}C$  

 Total Device Power Dissipation
 1

 Watt
  $50 \ mA$  

 \*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

 This is a stress rating only and functional operation of the device at these or other conditions beyond those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for ex 

## **RECOMMENDED DC OPERATING CONDITIONS**

 $(0^{\circ}C \leq T_A \leq 70^{\circ}C)$ 

SYM	PARAMETER	MIN	ТҮР	MAX	UNITS	NOTES
V <sub>CC</sub>	Supply Voltage	4.5	5.0	5.5	V	3
GND	Supply Voltage	0	0	0	V	
VIH	Logic 1 Voltage, All Inputs	2.2		V <sub>CC</sub> +1.0	V	3
VIL	Logic 0 Voltage, All Inputs	-0.1		0.8	V	3, 4

### **DC ELECTRICAL CHARACTERISTICS**

 $(0^{\circ}C \le T_A \le 70^{\circ}C) (V_{CC} = 5.0 \text{ V} \pm 10 \text{ percent})$ 

SYM	PARAMETER	MIN	MAX	UNITS	NOTES
I <sub>CC1</sub>	Average Power Supply Current		120	mA	5
I <sub>CC2</sub>	TTL Standby Current (MK41H67 only)		10	mA	6
I <sub>CC3</sub>	CMOS Standby Current (MK41H67 only)		50	μA	7
IIL	Input Leakage Current (Any Input Pin)	-1	+1	μA	8
IOL	Output Leakage Current (Any Output Pin)	-10	+10	μA	9
V <sub>OH</sub>	Output Logic 1 Voltage ( $I_{OUT} = -4 \text{ mA}$ )	2.4		V	3
VOL	Output Logic 0 Voltage (I <sub>OUT</sub> = +8 mA)		0.4	V	3



### CAPACITANCE

 $(T_A = 25 \,^{\circ}C, f = 1.0 \,\text{MHz})$ 

SYM	PARAMETER	ТҮР	MAX	UNITS	NOTES
C <sub>1</sub>	Capacitance on input pins	4	5	pF	10
C <sub>2</sub>	Capacitance on Q pins	8	10	pF	5, 10

### NOTES

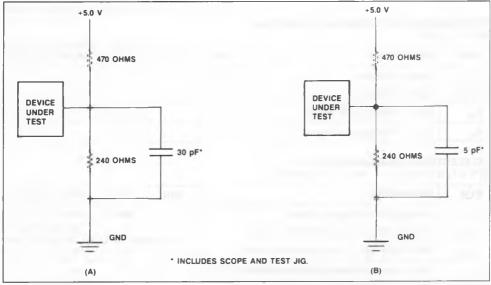
- 1. Measured with load shown in Figure 6(A).
- 2. Measured with load shown in Figure 6(B).
- 3. All voltages referenced to GND.
- V<sub>IL</sub> may undershoot to -2.0 volts for 200ns or less during input transitions.
- 5. I<sub>CC1</sub> is measured as the average AC current with V<sub>CC</sub> =  $V_{CC}$  (max) and with the outputs open circuit. tcycle = min. duty cycle 100%.
- 6. CE = VIH, All Other Inputs = Don't Care.

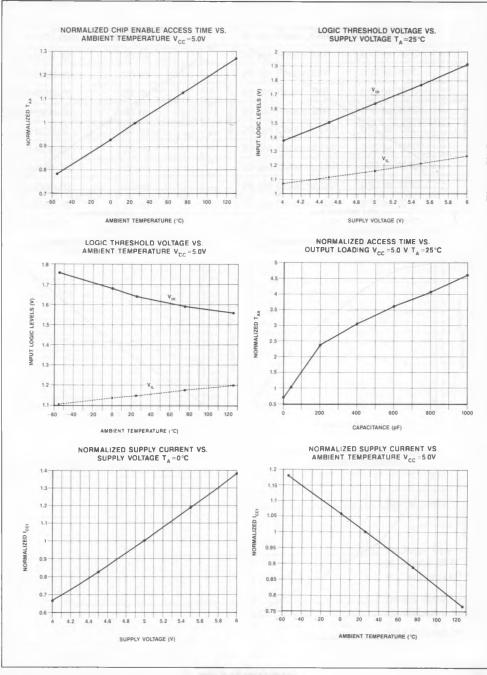
- 7. V<sub>CC</sub> (max) ≥CE ≥ V<sub>CC</sub> 0.3 V
- Input leakage current specifications are valid for all V<sub>IN</sub> such that 0 V < V<sub>IN</sub> < V<sub>CC</sub>. Measured at V<sub>CC</sub> = V<sub>CC</sub> (max).
- 9. Output leakage current specifications are valid for all V<sub>OUT</sub> such that 0 V < V<sub>OUT</sub> < V<sub>CC</sub>,  $\overline{CE/CS} = V_{IH}$  and V<sub>CC</sub> in valid operating range.
- 10. Capacitances are sampled and not 100% tested.

# **AC TEST CONDITIONS**

Input Levels	GND to 3.0 V
Transition Times	
Input and Output Signal Timing Reference Level	<b>1.5</b> V
Ambient Temperature	0°C to 70°C
V <sub>cc</sub>	± 10 percent

#### FIGURE 6. OUTPUT LOAD CIRCUITS

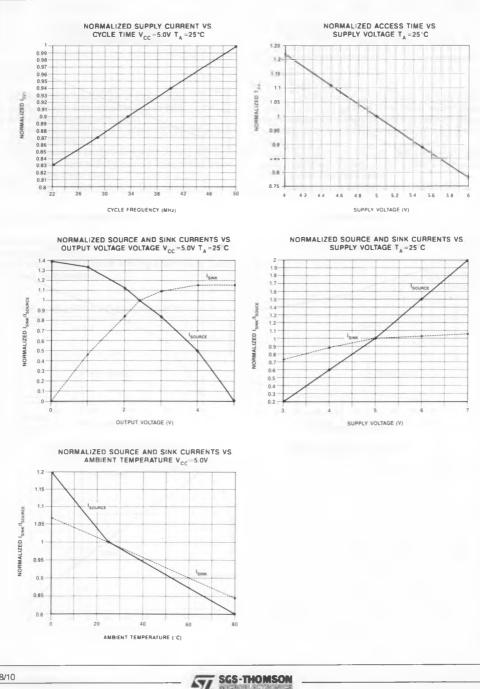




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#### NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS

### NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS



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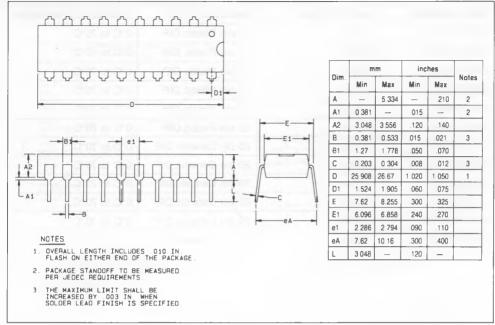
# ORDERING INFORMATION

PART NUMBER	ACCESS TIME	PACKAGE TYPE	TEMPERATURE RANGE
MK41H67N-20	20 ns	20 pin Plastic DIP	0°C to 70°C
MK41H67N-25	25 ns	20 pin Plastic DIP	0°C to 70°C
MK41H67N-35	35 ns	20 pin Plastic DIP	0°C to 70°C
MK41H66N-20	20 ns	20 pin Plastic DIP	0°C to 70°C
MK41H66N-25	25 ns	20 pin Plastic DIP	0°C to 70°C
MK41H66N-35	35 ns	20 pin Plastic DIP	0°C to 70°C
MK41H67P-20	20 ns	20 pin Ceramic DIP	0°C to 70°C
MK41H67P-25	25 ns	20 pin Ceramic DIP	0°C to 70°C
MK41H67P-35	35 ns	20 pin Ceramic DIP	0°C to 70°C
MK41H66P-20	20 ns	20 pin Ceramic DIP	0°C to 70°C
MK41H66P-25	25 ns	20 pin Ceramic DIP	0°C to 70°C
MK41H66P-35	35 ns	20 pin Ceramic DIP	0°C to 70°C

МК	41H6X N 20	
		Speed grade
		Package Type N: Plastic DIP P: Ceramic DIP
		Device family and identification number
		SGS-THOMSON prefix



### 20 PIN "N" PACKAGE, PLASTIC DIP



### 20 PIN "P" PACKAGE, SIDE BRAZED CERAMIC DIP

